



IDC04S60CE

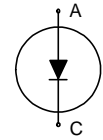
2nd generation thinQ!TM SiC Schottky Diode

Features:

- Revolutionary Semiconductor Material - Silicon Carbide
- Switching Behaviour Benchmark
- No Reverse Recovery / No Forward Recovery
- Temperature Independent Switching Behaviour
- Qualified According to JEDEC¹⁾ Based on Target Applications

Applications:

- SMPS, PFC, snubber



Chip Type	V_R	I_{Fn}	Die Size	Package
IDC04S60CE	600V	4A	1.146 x 0.968 mm ²	sawn on foil

Mechanical Parameters

Die size	1.146x 0.968		mm ²
Area total	1.11		
Anode pad size	0.909 x 0.731		
Thickness	355		µm
Wafer size	100		mm
Max. possible chips per wafer	6190		
Passivation frontside	Photoimide		
Pad metal	3200 nm AlSiCu		
Backside metal	Ni Ag –system		
Die bond	Electrically conductive epoxy glue and soft solder		
Wire bond	Al, ≤500µm		
Reject ink dot size	Ø 0.65mm; max 1.2mm		
Storage environment ¹⁾	for original and sealed MBB bags	Ambient atmosphere air, Temperature 17°C – 25°C, < 6 month	
	for open MBB bags	Acc. to IEC60721-3-3: Atmosphere >99% Nitrogen or inert gas, Humidity <25%RH, Temperature 17°C – 25°C, < 6 month	

¹⁾ Designed for storage conditions according to Infineon TR14 (Application Note "Storage of Products Supplied by Infineon Technologies")

Designed for climate condition under operation according to IEC60721-3-3, class 3K3



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Maximum Ratings

Parameter	Symbol	Condition	Value	Unit
Repetitive peak reverse voltage	V_{RRM}	$T_{vj} = 25^\circ\text{C}$	600	V
DC blocking voltage	V_{DC}		600	
Continuous forward current, limited by T_{vjmax}	I_F	$T_{vj} < 150^\circ\text{C}$	4	A
Surge non repetitive forward current, sine halfwave	$I_{F,SM}$	$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}$	32	
		$T_C = 150^\circ\text{C}, t_p = 10\text{ ms}$		
Repetitive peak forward current, limited by thermal resistance R_{th}	$I_{F,RM}$	$T_C = 100^\circ\text{C}, T_{vj} = 150^\circ\text{C}, D = 0.1$	18	
Non-repetitive peak forward current	$I_{F,max}$	$T_C = 25^\circ\text{C}, t_p = 10\mu\text{s}$	132	
i^2t value	$\int i^2 dt$	$T_C = 25^\circ\text{C}, t_p = 10\text{ ms}$	5.1	A ² s
		$T_C = 150^\circ\text{C}, t_p = 10\text{ ms}$		
Operating junction and storage temperature range	T_{vj}, T_{stg}		-55...+175	°C

Static Characteristics (tested on wafer), $T_{vj} = 25^\circ\text{C}$

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Reverse current	I_R	$V_R = 600\text{V}$		0.5	50	μA
Diode forward voltage	V_F	$I_F = 4\text{A}$		1.7	1.9	V

Static Characteristics (not subject to production test - verified by design / characterization)

Parameter	Symbol	Conditions	Value			Unit
			min.	Typ.	max.	
Reverse current	I_R	$V_R = 600\text{V}, T_{vj} = 150^\circ\text{C}$		2	500	μA
Diode forward voltage	V_F	$I_F = 4\text{A}, T_{vj} = 150^\circ\text{C}$		2	2.4	V



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Dynamic Characteristics (not subject to production test - verified by design / characterization)

Parameter	Symbol	Conditions		Value			Unit
				min.	Typ.	max.	
Total capacitive charge ³⁾	Q_C	$I_F \leq I_{F,max}$ $di/dt = 200 A/\mu s$ $V_R = 400 V$	$T_{vj} = 150^\circ C$		8		nC
Switching time ²⁾	t_c		$T_{vj} = 150^\circ C$			<10	ns
Total capacitance	C	$f = 1 MHz$	$V_R = 1 V$		130		pF
			$V_R = 300 V$		20		
			$V_R = 600 V$		20		

¹⁾ J-STD20 and JESD22

²⁾ t_c is the time constant for the capacitive displacement current waveform (independent from $T_{vj} = 150^\circ C$, I_{LOAD} and di/dt), different from t_{tr} , which is dependent on $T_{vj} = 150^\circ C$, I_{LOAD} , di/dt . No reverse recovery time constant t_{tr} due to absence of minority carrier inject.

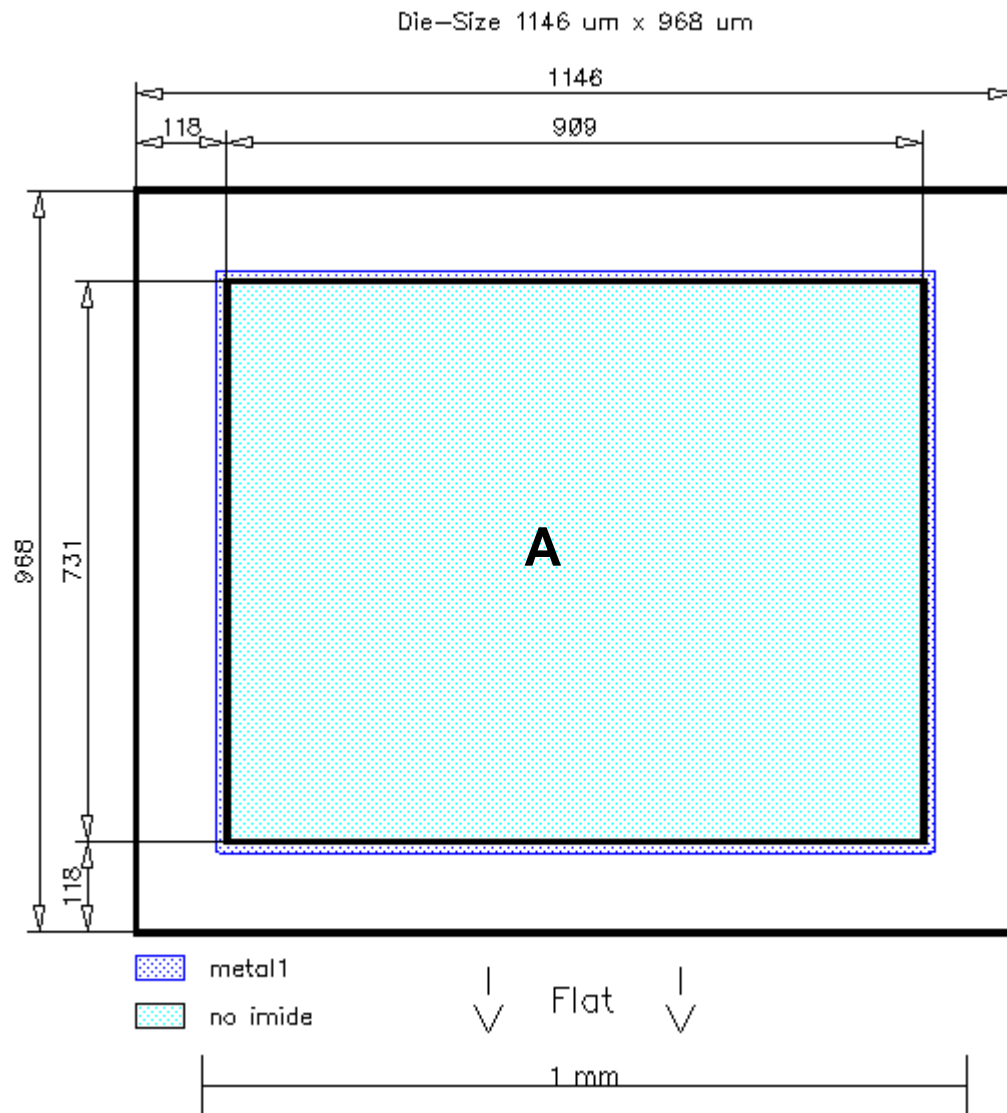
³⁾ Only capacitive charge occurring, guaranteed by design (independent from T_{vj} , I_{LOAD} and di/dt).

Further Electrical Characteristics

Switching characteristics and thermal properties are depending strongly on module design and mounting technology and can therefore not be specified for a bare die.

This chip data sheet refers to the device data sheet	IDT04S60C	Rev. 2.1
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Chip Drawing



A: Anode pad



IDC04S60CE

Description

AQL 0,65 for visual inspection according to failure catalogue

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Revision History

Version	Subjects (major changes since last revision)	Date

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